



AMP3112P SOLID STATE HIGH POWER AMPLIFIER

FEATURES

- Class AB linear GaN design
- Instantaneous bandwidth
- Suitable for X-Band linear short pulse applications
- Small form factor and light weight
- Built-in protection circuits
- High reliability and ruggedness



ELECTRICAL SPECIFICATIONS: 50Ω, 25°C

Parameter	Specification	Notes
Operating Frequency Range	9.5 - 10.0 GHz	
Pulse Power Output	300 Watt Min	Peak pulse
Power Gain	55 dB Min	
Power Gain Flatness	3.0 dB p-p Max	
Input Pulse Characteristics	Width	PRF
	0.2 - 2 μS	1 KHz
Input / Output Return Loss	-10 dB Max	Relative to 50 Ohm
Harmonics	-30 dBc Typ	At rated Pout
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	32 VDC Nom	
Current Consumption	10 Amp Avg Max	At rated Pout
Input Power Protection	+3 dBm Max	<10 Sec without damage
Load VSWR Protection	3 : 1 Max	<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +65 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	220 x 235 x 27 mm	
Weight	3 Kg.	
RF Connectors In/Out	Hi-Freq. SMA female	Optional WG (WR90)
DC Power / Interface Connector	7-Pin Hybrid D-Sub	
Cooling	External Heatsink	Forced air required

D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	N/C	
2	N/C	
3	CURRENT SENSOR	I _D @50mV/100mA Typ
4	TEMP SENSOR	V _T @10mV/°C + 500mV Typ
5	SHUTDOWN	TTL "Hi" = Disable Function @ <50mS
A1	VDD	32VDC
A2	GND	Ground

OUTLINE DRAWING

